



# گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما



09153223758



051-37581400



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مشهد خیام شمالی 63 خیابان پردیس 3

برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
- آموزش تخصصی ابراز آلات شارژی



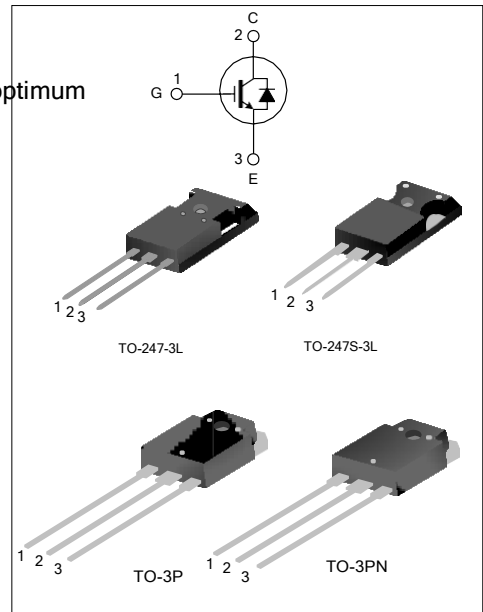
## 60A, 600V FIELD STOP IGBT

### DESCRIPTION

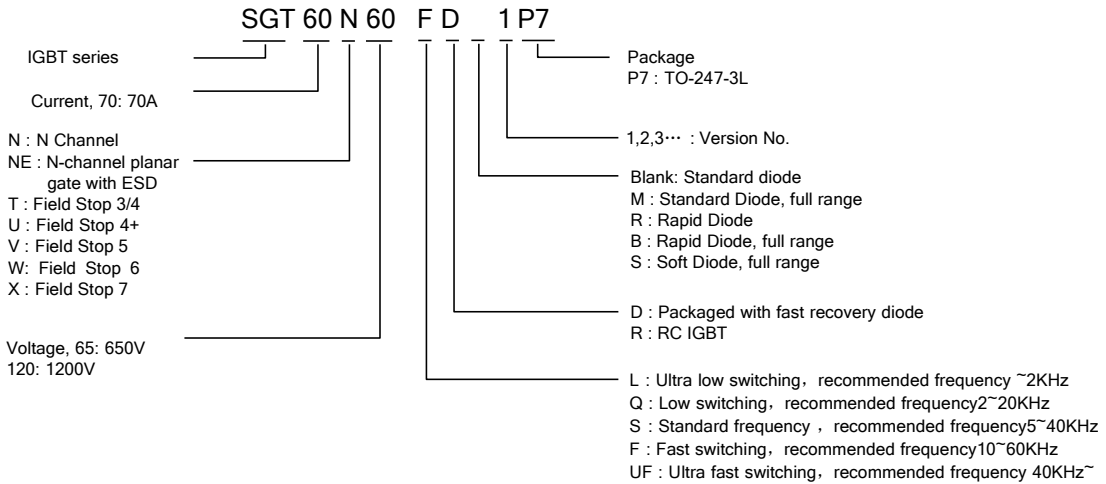
SGT60N60FD1PN/P7/PS/PT adopts Field Stop IGBT technology, offer the optimum performance for induction Heating, UPS, SMPS and PFC application.

### FEATURES

- ◆ 60A, 600V,  $V_{CE(sat)(typ.)}=2.2V@I_C=60A$
- ◆ Low conduction loss
- ◆ Fast switching
- ◆ High input impedance



### NOMENCLATURE



### ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SGT60N60FD1PN	TO-3P	60N60FD1	Pb free	Tube
SGT60N60FD1P7	TO-247-3L	60N60FD1	Pb free	Tube
SGT60N60FD1PS	TO-247S-3L	60N60D1	Pb free	Tube
SGT60N60FD1PT	TO-3PN	60N60FD1	Pb free	Tube



ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

Characteristics		Symbol	Ratings	Units
Collector to Emitter Voltage		$V_{CE}$	600	V
Gate to Emitter Voltage		$V_{GE}$	$\pm 20$	V
Collector Current	$T_C=25^\circ\text{C}$	$I_C$	120	A
	$T_C=100^\circ\text{C}$		60	
Pulsed Collector Current		$I_{CM}$	180	A
Maximum Power Dissipation ( $T_C=25^\circ\text{C}$ )		$P_D$	321	W
Operating Junction Temperature		$T_J$	$-55 \sim +175$	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	$-55 \sim +175$	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings	Units
Thermal Resistance, Junction to Case(IGBT)(TO-3P)	$R_{\theta JC}$	0.39	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case(FRD)(TO-3P)	$R_{\theta JC}$	1.10	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient(TO-3P)	$R_{\theta JA}$	40	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS OF IGBT( $T_C=25^\circ\text{C}$ , UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Units
Collector to Emitter Breakdown Voltage	$BV_{CE}$	$V_{GE}=0V, I_C=250\mu\text{A}$	600	--	--	V
C-E Leakage Current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$	--	--	200	$\mu\text{A}$
G-E Leakage Current	$I_{GES}$	$V_{GE}=20V, V_{CE}=0V$	--	--	$\pm 400$	nA
G-E Threshold Voltage	$V_{GE(th)}$	$I_C=250\mu\text{A}, V_{CE}=V_{GE}$	4.0	5.0	6.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=60A, V_{GE}=15V$	--	2.2	2.7	V
		$I_C=60A, V_{GE}=15V, T_C=125^\circ\text{C}$	--	2.6	--	V
Input Capacitance	$C_{ies}$	$V_{CE}=30V$	--	2850	--	pF
Output Capacitance	$C_{oes}$	$V_{GE}=0V$	--	294	--	
Reverse Transfer Capacitance	$C_{res}$	$f=1\text{MHz}$	--	85	--	
Turn-On Delay Time	$T_{d(on)}$	$V_{CE}=400V$ $I_C=60A$ $R_g=10\Omega$	--	36	--	ns
Rise Time	$T_r$		--	142	--	
Turn-Off Delay Time	$T_{d(off)}$		--	193	--	
Fall Time	$T_f$		--	136	--	
Turn-On Switching Loss	$E_{on}$	$V_{GE}=15V$	--	3.72	--	mJ
Turn-Off Switching Loss	$E_{off}$	Inductive Load,	--	1.77	--	
Total Switching Loss	$E_{st}$		--	5.49	--	
Total Gate Charge	$Q_g$	$V_{CE}=400V, I_C=60A,$ $V_{GE}=15V$	--	179	--	nC
Gate to Emitter Charge	$Q_{ge}$		--	23	--	
Gate to Collector Charge	$Q_{gc}$		--	100	--	

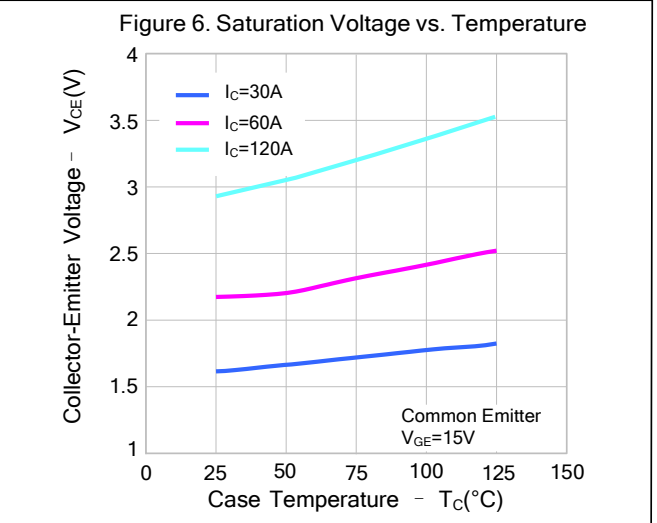
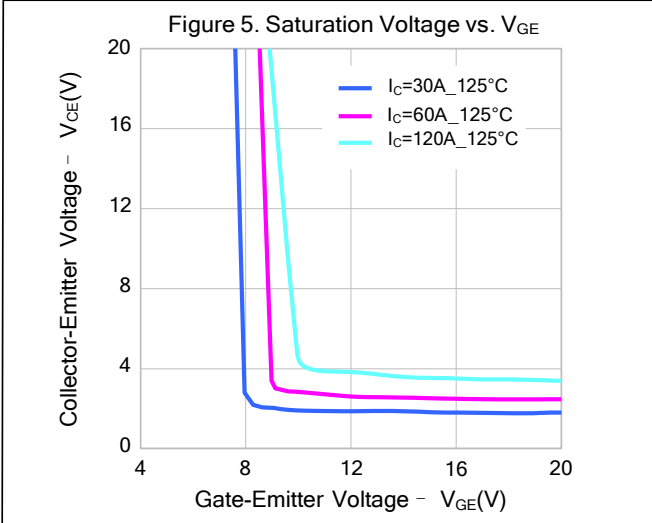
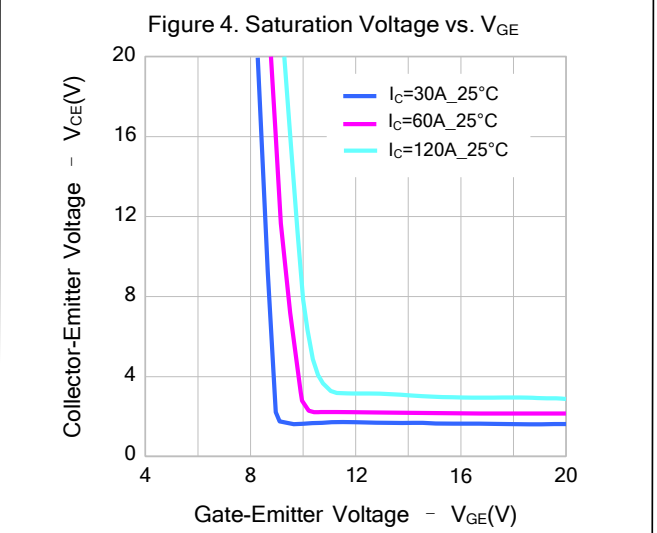
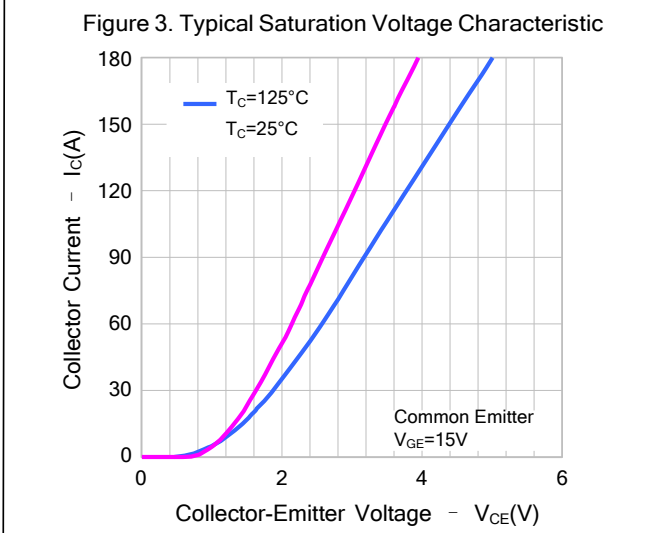
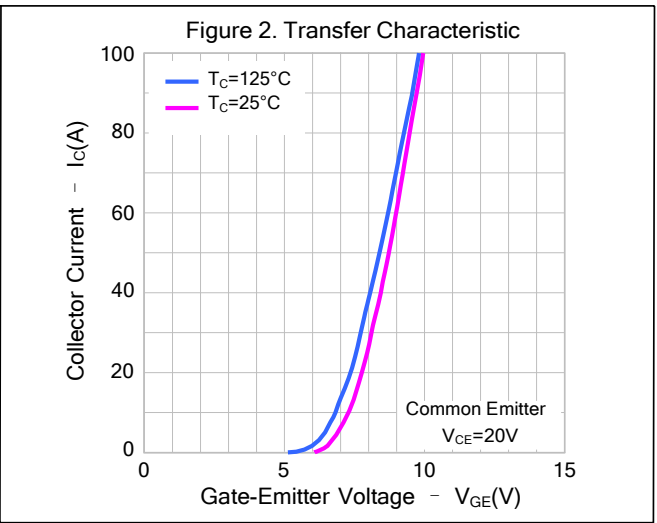
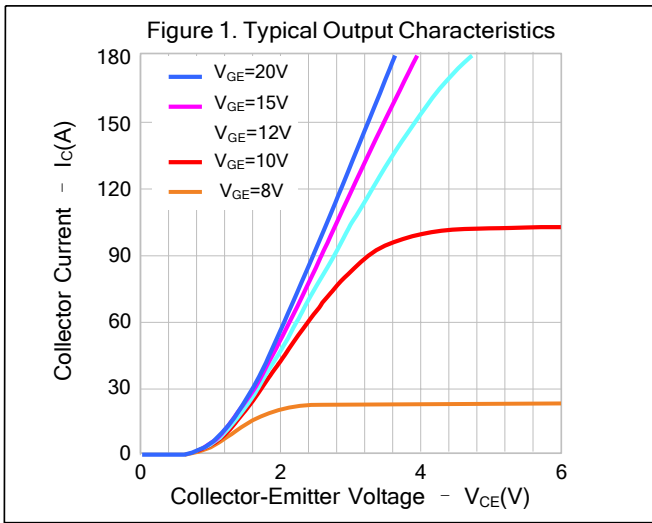


## ELECTRICAL CHARACTERISTICS OF FRD( $T_C=25^{\circ}\text{C}$ UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Units
Diode Forward Voltage	$V_{FM}$	$I_F=30\text{A}, T_C=25^{\circ}\text{C}$	--	1.9	2.6	V
		$I_F=30\text{A}, T_C=125^{\circ}\text{C}$	--	1.5	--	
Diode Reverse Recovery Time	$T_{rr}$	$I_{ES}=30\text{A}, dI_{ES}/dt=200\text{A}/\mu\text{s}$	--	38	--	ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_{ES}=30\text{A}, dI_{ES}/dt=200\text{A}/\mu\text{s}$	--	85	--	nC



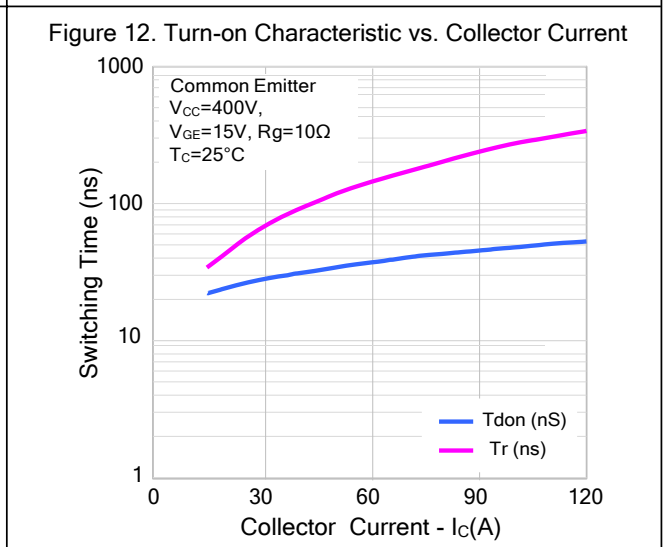
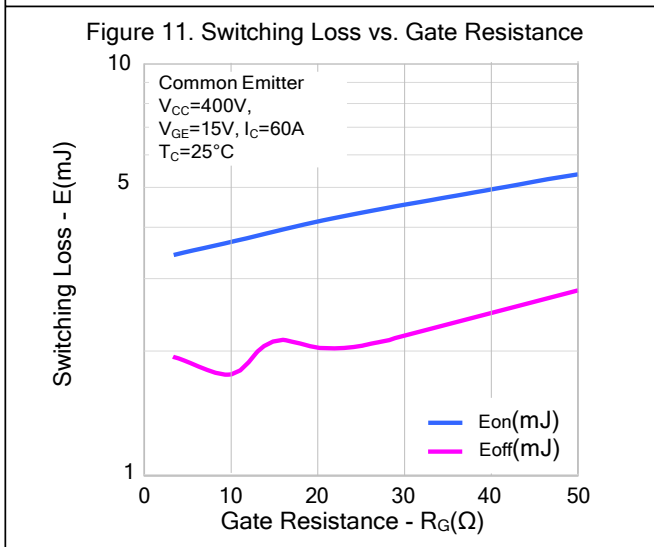
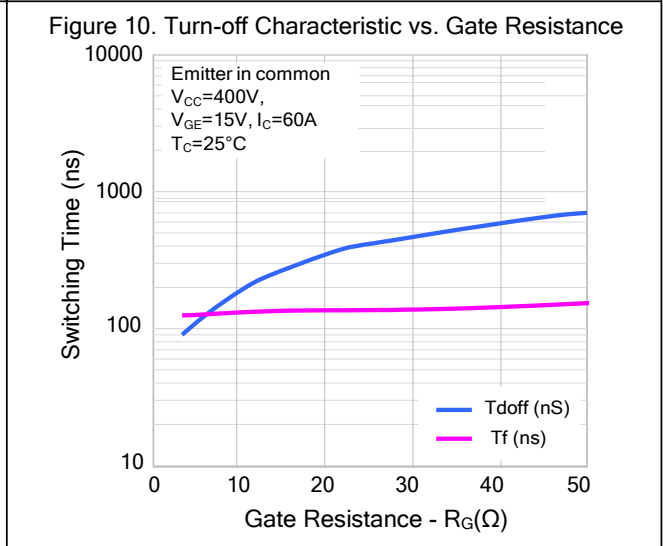
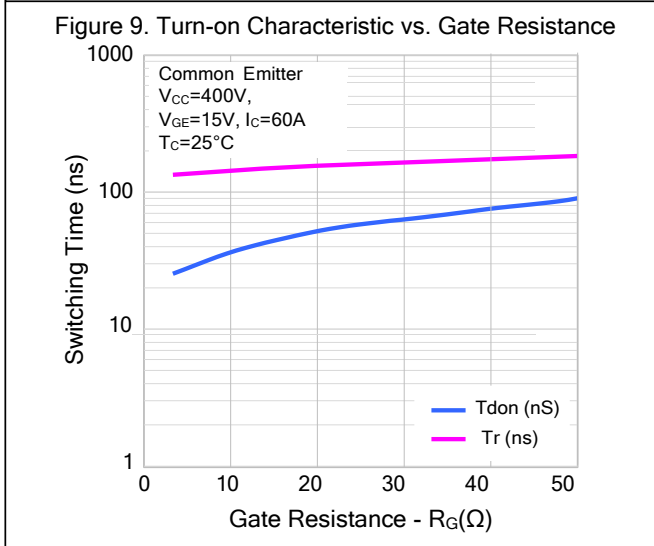
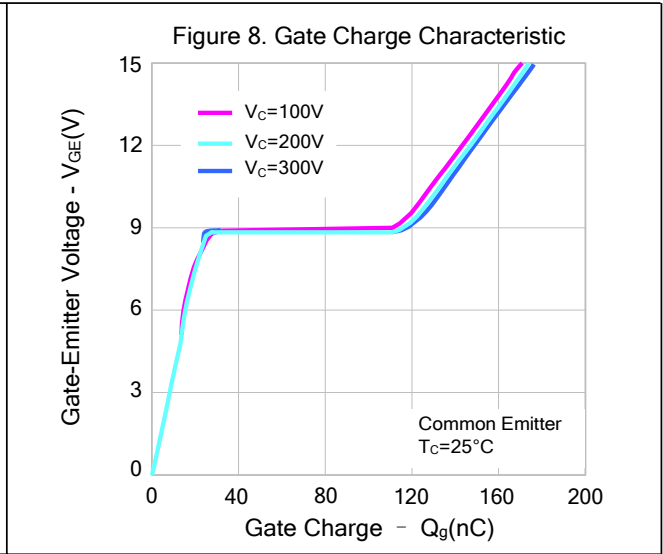
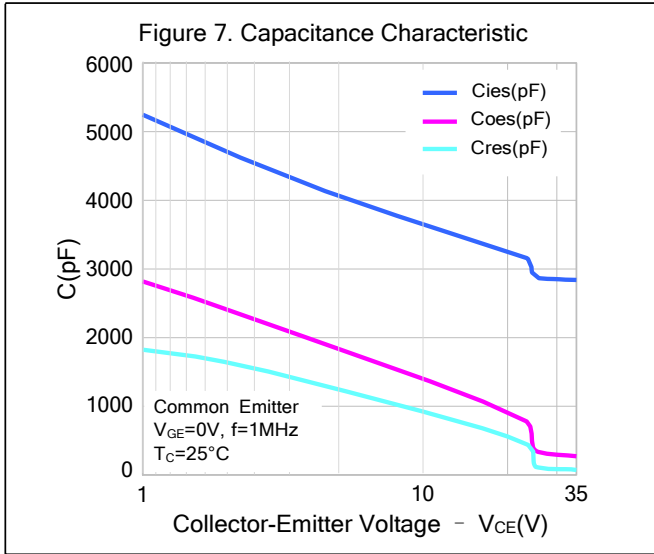
TYPICAL CHARACTERISTICS CURVE





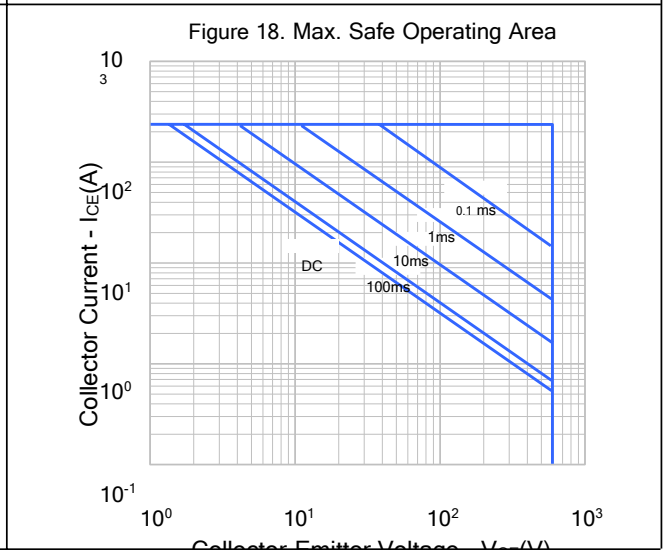
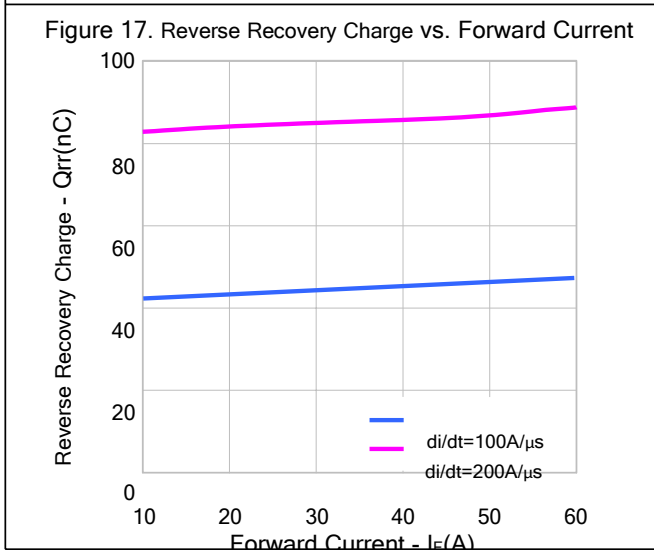
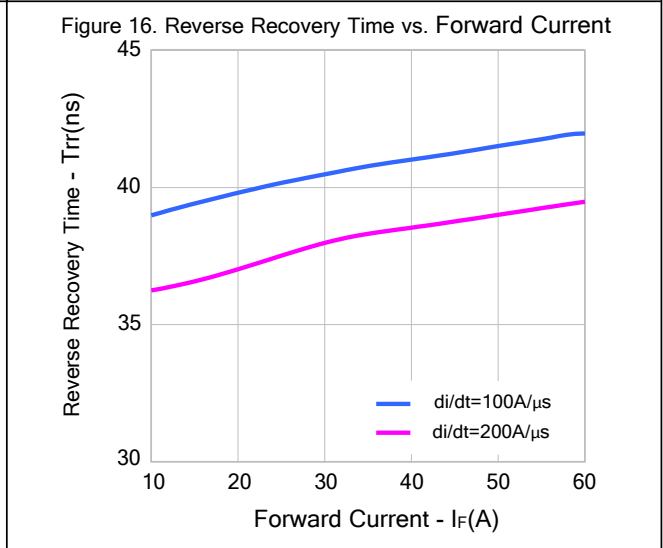
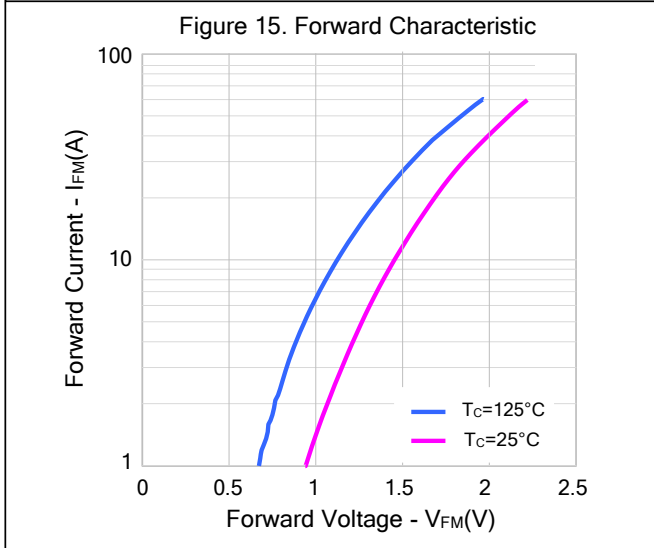
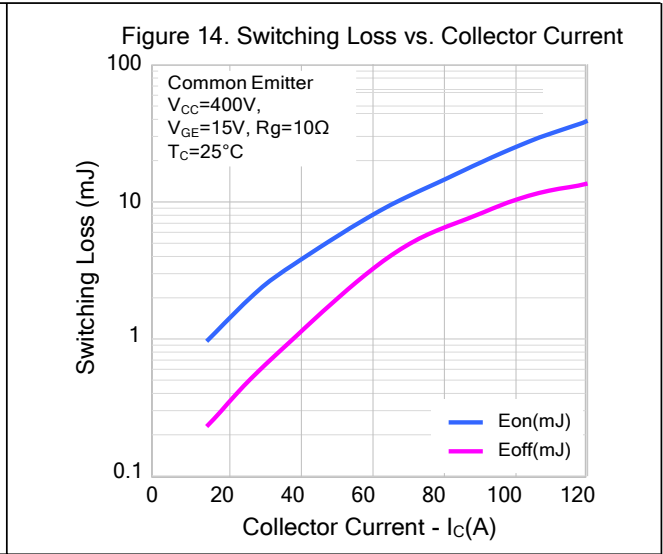
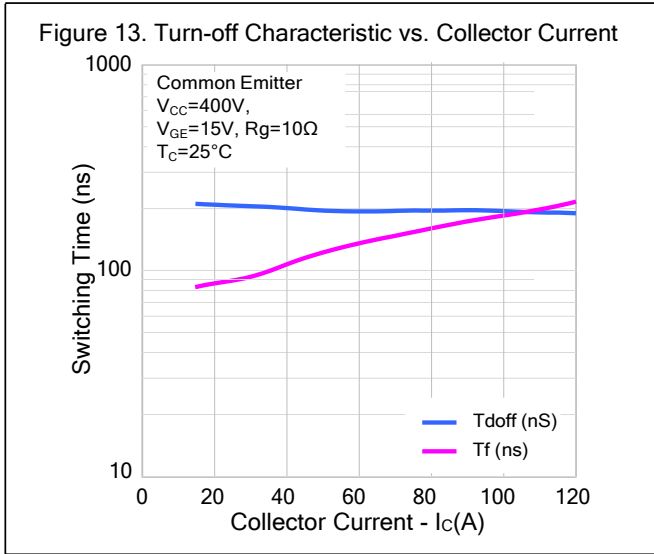


TYPICAL CHARACTERISTICS CURVE (CONTINUED)





TYPICAL CHARACTERISTICS CURVE (CONTINUED)





TYPICAL CHARACTERISTICS CURVE (CONTINUED)

Figure 19. Square Wave Impedance Simulation (IGBT)

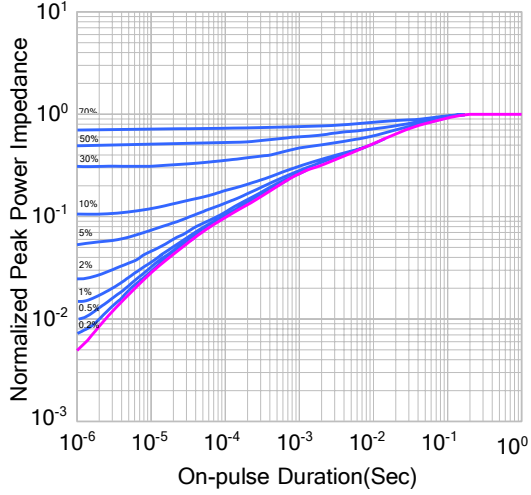
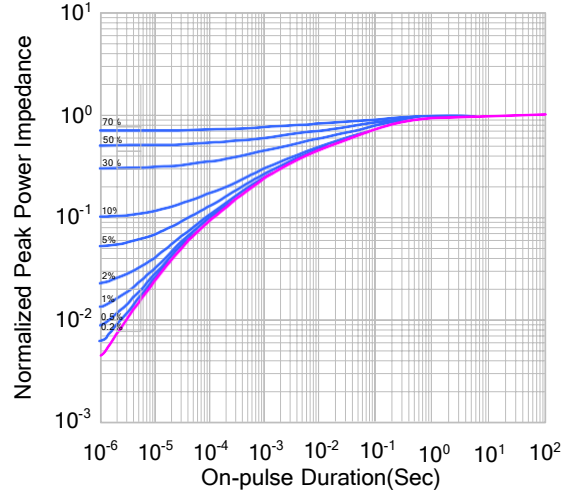


Figure 20. Square Wave Impedance Simulation (FRD)







PACKAGE OUTLINE

**TO-3P** Unit: mm

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.4	—	5.2
C1	1.2	—	1.8
A1	1.2	—	2.0
b	0.7	1.0	1.3
b1	2.7	3.0	3.3
b2	1.7	2.0	2.3
D	15.0	15.5	16.0
C	0.4	0.6	0.8
F2	8.5	—	10.0
e	5.45 TYP		
L1	22.6	—	23.6
L	39.0	—	41.5
L2	19.5	—	21.0

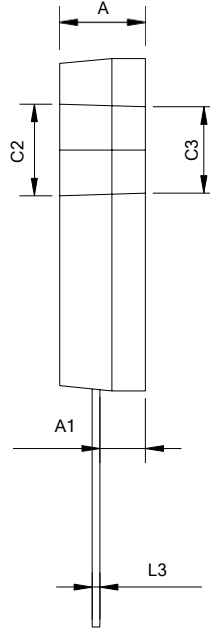
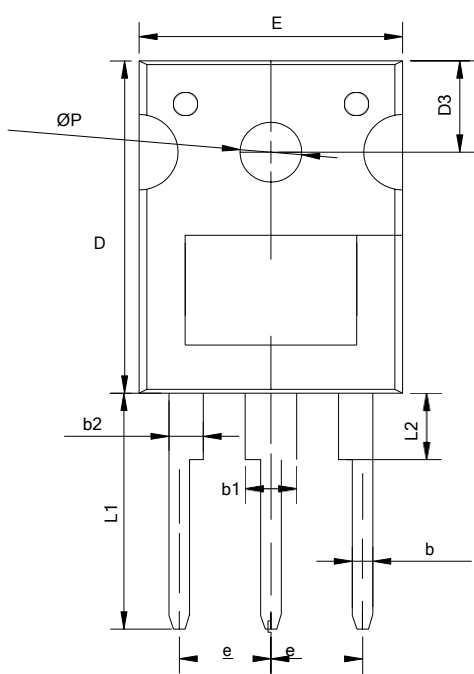
**TO-247-3L** Unit: mm

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	—	1.36
b2	1.91	—	2.25
b4	2.91	—	3.25
c	0.51	—	0.75
D	20.80	21.00	21.30
E	15.50	15.80	16.10
E2	4.40	5.00	5.20
e	5.44 BSC		
L	19.72	19.92	20.22
L1	—	—	4.30
Q	5.60	5.80	6.00



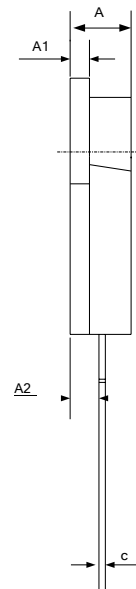
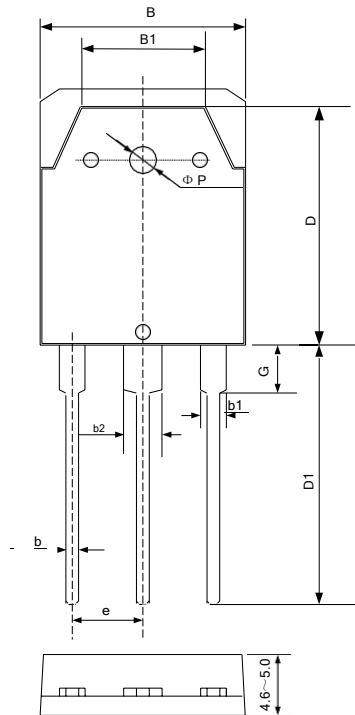
PACKAGE OUTLINE(CONTINUED)

TO-247S-3L Unit: mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.30	2.50	2.70
b	1.10	1.20	1.30
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c2	5.50	6.00	6.50
c3	4.95	5.10	5.25
D	19.00	20.00	21.00
D3	5.30	5.50	5.70
e	5.34	5.44	5.54
E	15.40	15.60	15.80
L1	14.40	14.60	14.80
L2	3.85	4.00	4.15
L3	0.35	0.50	0.65
ØP	3.40	3.60	3.80

TO-3PN Unit: mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.60	4.80	5.00
A1	1.30	1.50	1.70
A2	2.20	2.40	2.60
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.90	3.10	3.30
B	15.20	15.60	16.00
B1	9.10	9.30	9.50
c	0.50	0.60	0.70
D	18.30	18.50	18.70
D1	19.00	19.50	20.00
e	5.25	5.45	5.65
G	2.80	3.00	3.20
ØP	3.00	3.20	3.40



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Rev.: 1.7

Revision History:

1. Add package outline of TO-3PN
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Rev.: 1.6

Revision History:

1. Add package outline of TO-247S-3L
- 

Rev.: 1.5

Revision History:

1. Modify Package stereogram and Important notice
- 

Rev.: 1.4

Revision History:

1. Update the package outline of TO-247-3L
- 

Rev.: 1.3

Revision History:

1. Modify the Max Value of Junction Temperature
- 

Rev.: 1.2

Revision History:

1. Modify annotation of Fig.13
- 

Rev.: 1.1

Revision History:

1. Modify the characteristics
- 

Rev.: 1.0

Revision History:

1. First release
- 
-